



INFORMATION DISCLOSURE CITATION PTO-1449 21 JULY 2004	CUSTOMER NUMBER 26615	ATTORNEY'S DKT NO. H1108C	APPLICATION NO. 10/830,006
		APPLICANT(S) Zoran KRIVOKAPIC et al.	
		FILING DATE April 23, 2004	GROUP 2818

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TH	2002/0140039	10/3/02	Ballantine et al. Adkisson			
	2002/0130354	9/19/02	Ishii et al. Setigawa			
	6,475,869	11/5/02	Yu	438	303	
	6,458,662	10/1/02	Yu		286	
	6,300,182	10/9/01	Yu		217	
TH	5,757,038	5/26/98	Wind et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes No
TH	EP 1 202 335	5/2/02	Adkisson et al.			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED
TH	11/02/04

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SHEET 1 OF 1

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GROUP
Unassigned 2818

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TH	6,709,982	03-2004	Buynoski et al.	438	696	
	6,706,571	03-2004	Yu et al.	438	157	
	6,657,252	12-2003	Fried et al.	257	316	
	6,642,090	11-2003	Fried et al.	438	164	
	6,645,797	11-2003	Buynoski et al.	438	157	
	6,657,259	12-2003	Fried et al.	257	350	
TH	6,630,388	10-2003	Sekigawa et al.	438	396	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED
TH - THe + 10	Nov 2004

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INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number 26615	ATTORNEY'S DKT No. H1108C	CONTINUATION APPLICATION OF SERIAL NO. 10/348,910		
			APPLICANT(S) Zoran Krivokapić et al.	FILING DATE April 23, 2004	GROUP 2818 Unassigned	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TH	6,583,469 B1	06-24-03	Fried et al.	257	329	01-28-02
TH	US 2004/0048424 A1	03-11-04	Wu et al.	438	154	09-05-02
TH	US 2003/0042531 A1	03-06-03	Lee et al.	257	315	09-04-02
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						Yes
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
TH	Digh Hisamoto et al.: "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.					
	Yang-Kyu Choi et al.: "Sub-20nm CMOS Fin FET Technologies," 0-7803-5410-9/99 IEEE, March 2001, 4 pages.					
	Xuejue Huang et al.: "Sub-50 nm P-Channel Fin FET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.					
	Yang-Kyu Choi et al.: "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.					
	Xuejue Huang et al.: "Sub 50-nm FinFET: PMOS," 0-7803-7050-3/01 IEEE, September 1999 4 pages.					
	Co-pending U.S. Application Serial No. 10/614,052 filed July 8, 2003 titled "Narrow Fins By Oxidation In Double-Gate FinFet," 11 page specification, 7 sheets of drawings.					
TH	Co-pending U.S. Application Serial No. 10/699,887 filed November 4, 2003 titled "Self Aligned Damascene Gate," 35 pages.					
EXAMINER Tu-Tu Ho	DATE CONSIDERED Nov 2004					

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